NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **MRF323** is Designed for Wide Band Large-Signal Driver and Predriver Applications in the 200 to 500 MHz Range.

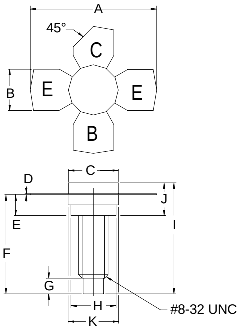
FEATURES INCLUDE:

- Gold Metalization
- **30:1 VSWR**

MAXIMUM RATINGS

I_C	2.2 A (CONT) 3.0 A (PEAK)
V_{CB}	60 V
P_{DISS}	55 W @ T_C = 25 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	3.2 °C/W

PACKAGE STYLE .280" 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.055 / 26.80
B	.220 / 5.59	.230 /5.84
C	.270 / 6.86	.285 / 7.24
D	.003 / 0.08	.007 / 0.18
E	.117 / 2.97	.137 / 3.48
F	.572 / 14.53	
G	.130 / 3.30	
H	.245 / 6.22	.255 / 6.48
I	.640 / 16.26	
J	.175 / 4.45	.217 / 5.51
K	.275 / 6.99	.285 / 7.24

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 20 mA	60			**V**
BV_{CES}	I_C = 20 mA	60			**V**
BV_{CEO}	I_C = 20 mA	33			**V**
BV_{EBO}	I_E = 2.0 mA	4.0			**V**
I_{CBO}	V_{CB} = 30 V			2.0	**mA**
h_{FE}	I_C = 1.0 A V_{CE} = 5.0 V	20		80	**---**
C_{ob}	V_{CB} = 28 V f = 1.0 MHz		20	24	**pF**
G_{PE} **η**	V_{CC} = 28 V P_{out} = 20 W f = 400 MHz	10 50	11 60		**dB** **%**
ψ	V_{CC} = 28 V P_{out} = 20 W f = 400 MHz VSWR = 30:1 ALL PHASE ANGLES	NO DEGRADATION IN OUTPUT POWER			